KISAB

PRODUCT SPECIFICATIONS

Product specifications

Silicon carbide substrate material specification

Property	Value
Polytype	4H polytype
Orientation	4° offcut
Diameter	150 ±0.05mm
Center thickness	350+/- 10µm
Warp	<40µm
TTV	<6 µm
Surface treatment (Si-face)	Epi-ready
Resistivity	19-21 mΩcm^{-1}
Resistivity uniformity	<2%
Edge exclusion	3 mm

Defect density

Property	Value
Micropipes (MP)	<0.1 cm^{-2}
Basal plane dislocation density (BPD) - 80% of wafer area	None
Threading dislocation density (TD)	<4'000 cm^{-2}

Packaging

Cassettes or single wafers